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REPLY UNDER 37 CFR 1.116
EXPEDITED PROCEDURE
TECHNOLOGY CENTER 2800

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of: William G. America Conf. No.: 3775
 Serial No.: 10/709,776 Art Unit: 2811
 Filed: 5/27/2004 Dkt. #: FIS920040083US1 (IBMF-0058)
 Title: SEMICONDUCTOR DEVICE FORMED
 BY IN-SITU MODIFICATION OF
 DIELECTRIC LAYER AND RELATED
 METHODS Examiner: Im, Junghwa M

Mail Stop AF
 Commissioner for Patents
 P.O. Box 1450
 Alexandria, VA 22313-1450

entered
 w/ RCE
 9/5/06
 JF

AFTER-FINAL AMENDMENT

Sir:

I. INTRODUCTORY COMMENTS

This paper is being filed in response to the Final Office Action dated June 05, 2006.

Please amend the above-referenced patent application as follows:

10/709,776

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